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Attorney's Docket No.: 07977-093002 / US3164D1



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Hisashi Ohtani, et al. Art Unit : 2815  
Serial No.: 09/379,702 Examiner : Eugene Lee  
Filed : August 24, 1999  
Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICES

Commissioner for Patents  
Washington, D.C. 20231

RESPONSE

In response to the action mailed February 14, 2002, please amend the application as follows:

In the claims:

Please cancel all pending claims, specifically claims 2-12, 14-25, 27, 28, and 30-44.

Please substitute new claims 45-64 as follows:

*sub G1*  
*E1*  
over

--45. A semiconductor device comprising:  
a crystalline semiconductor island comprising silicon  
a substrate, the crystalline semiconductor island comprising a source region, a drain region and a channel formation region provided between the source and the drain region; and

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, Washington, D.C. 20231.

June 14, 2002

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